

NTMFD4C20N

Dual N-Channel Power MOSFET

30 V, High Side 18 A / Low Side 27 A, Dual N-Channel SO8FL

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

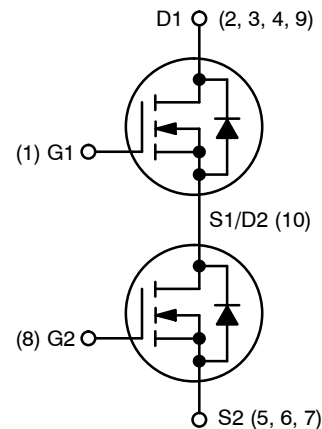
- DC-DC Converters
- System Voltage Rails
- Point of Load



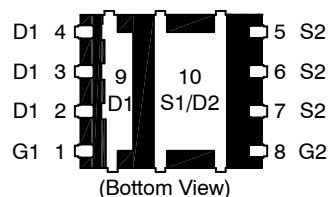
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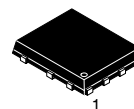
V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
Q1 Top FET 30 V	7.3 mΩ @ 10 V	18 A
	10.8 mΩ @ 4.5 V	
Q2 Bottom FET 30 V	3.4 mΩ @ 10 V	27 A
	5.2 mΩ @ 4.5 V	



PIN CONNECTIONS



MARKING DIAGRAM



DFN8
CASE 506BX



4C20N = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage	Q1		V_{DSS}	30	V
Drain-to-Source Voltage	Q2				
Gate-to-Source Voltage	Q1		V_{GS}	± 20	V
Gate-to-Source Voltage	Q2				
Continuous Drain Current $R_{\theta JA}$ (Note 1)		$T_A = 25^\circ\text{C}$	Q1	12	A
			Q2	18	
		$T_A = 85^\circ\text{C}$	Q1	8.6	
			Q2	13	
Power Dissipation $R_{\theta JA}$ (Note 1)		$T_A = 25^\circ\text{C}$	Q1	1.88	W
			Q2	1.97	
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)		$T_A = 25^\circ\text{C}$	Q1	18.2	A
			Q2	27.4	
		$T_A = 85^\circ\text{C}$	Q1	13.1	
			Q2	19.8	
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)		$T_A = 25^\circ\text{C}$	Q1	4.37	W
			Q2	4.6	
Continuous Drain Current $R_{\theta JA}$ (Note 2)		$T_A = 25^\circ\text{C}$	Q1	9.1	A
			Q2	13.7	
		$T_A = 85^\circ\text{C}$	Q1	6.6	
			Q2	9.9	
Power Dissipation $R_{\theta JA}$ (Note 2)		$T_A = 25^\circ\text{C}$	Q1	1.09	W
			Q2	1.15	
Pulsed Drain Current		$T_A = 25^\circ\text{C}$ $t_p = 10 \mu\text{s}$	Q1	55	A
			Q2	82	
Operating Junction and Storage Temperature	Q1		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
	Q2				
Source Current (Body Diode)	Q1		I_S	4.0	A
	Q2			4.2	
Drain to Source DV/DT			dV/dt	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = XX A_{pk}$, $L = 0.1$ mH, $R_G = 25 \Omega$)	18	Q1	EAS	16	mJ
	29	Q2	EAS	42	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	Q1	$R_{\theta JA}$	66.5	°C/W
	Q2		63.3	
Junction-to-Ambient – Steady State (Note 4)	Q1	$R_{\theta JA}$	114.3	
	Q2		108.7	
Junction-to-Ambient – ($t \leq 10$ s) (Note 3)	Q1	$R_{\theta JA}$	28.6	
	Q2		27.2	
Junction-to-Case – (Drain)	Q1	$R_{\theta JC}$	5.4	
	Q2		3.7	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	Q1	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
	Q2		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			
Drain-to-Source Breakdown Voltage Temperature Coefficient	Q1	$V_{(BR)DSS}/T_J$			14.5		mV/°C
	Q2				12		
Zero Gate Voltage Drain Current	Q1	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
				$T_J = 125^\circ\text{C}$		10	
	Q2		$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		10	
Gate-to-Source Leakage Current	Q1	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
	Q2					± 100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.3		2.1	V
	Q2			1.3		2.1	
Negative Threshold Temperature Coefficient	Q1	$V_{GS(TH)}/T_J$			4.7		mV/°C
	Q2				5.1		
Drain-to-Source On Resistance	Q1	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		5.8	7.3	mΩ
			$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		8.7	10.8	
	Q2		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		2.7	3.4	
			$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		4.0	5.2	
Forward Transconductance	Q1	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 10\text{ A}$		43		S
	Q2				68		

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit		
CHARGES, CAPACITANCES & GATE RESISTANCE									
Input Capacitance	Q1	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		970		pF		
	Q2				1950				
Output Capacitance	Q1	C _{OSS}			430				
	Q2				990				
Reverse Capacitance	Q1	C _{RSS}			125				
	Q2				50				
Total Gate Charge	Q1	Q _{G(TOT)}		V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 10 A		9.3			nC
	Q2					13			
Threshold Gate Charge	Q1	Q _{G(TH)}			1.6				
	Q2				3.3				
Gate-to-Source Charge	Q1	Q _{GS}			3.3				
	Q2				6.0				
Gate-to-Drain Charge	Q1	Q _{GD}			4.2				
	Q2				3.0				
Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V; I _D = 10 A		19		nC		
	Q2				29				

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 15 A, R _G = 3.0 Ω		9.0		ns
	Q2				11		
Rise Time	Q1	t _r			33		
	Q2				32		
Turn-Off Delay Time	Q1	t _{d(OFF)}			15		
	Q2				20		
Fall Time	Q1	t _f			5.0		
	Q2				5.0		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 15 A, R _G = 3.0 Ω		6.0		ns
	Q2				8.0		
Rise Time	Q1	t _r			26		
	Q2				26		
Turn-Off Delay Time	Q1	t _{d(OFF)}			18		
	Q2				25		
Fall Time	Q1	t _f			4.0		
	Q2				4.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Voltage	Q1	V _{SD}	V _{GS} = 0 V, I _S = 3 A	T _J = 25°C	0.75	1.0	V
				T _J = 125°C	0.62		
	Q2		V _{GS} = 0 V, I _S = 3 A	T _J = 25°C	0.45	0.70	
				T _J = 125°C	0.37		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	Q1	t _{RR}	V _{GS} = 0 V, d _{IS} /d _t = 100 A/μs, I _S = 30 A		23		ns
	Q2				38		
Charge Time	Q1	t _a			11.6		
	Q2				18.6		
Discharge Time	Q1	t _b			11.4		
	Q2				19.4		
Reverse Recovery Charge	Q1	Q _{RR}			10		nC
	Q2				25		

PACKAGE PARASITIC VALUES

Source Inductance	Q1	L _S	T _A = 25°C		0.38		nH	
	Q2				0.65			
Drain Inductance	Q1	L _D			0.054		nH	
	Q2				0.007			
Gate Inductance	Q1	L _G			1.5		nH	
	Q2				1.5			
Gate Resistance	Q1	R _G			0.3	1.0	2.0	Ω
	Q2				0.3	1.0	2.0	

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFD4C20NT1G	DFN8 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFD4C20N

TYPICAL CHARACTERISTICS – Q1

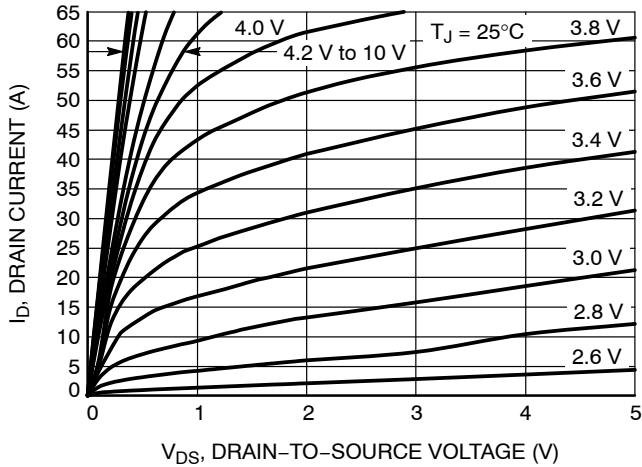


Figure 1. On-Region Characteristics

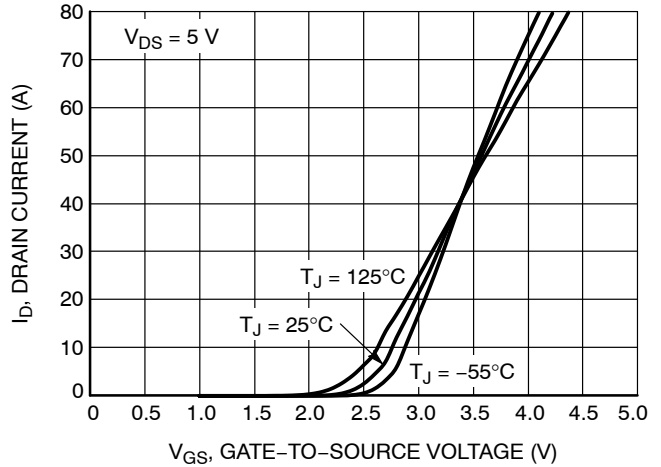


Figure 2. Transfer Characteristics

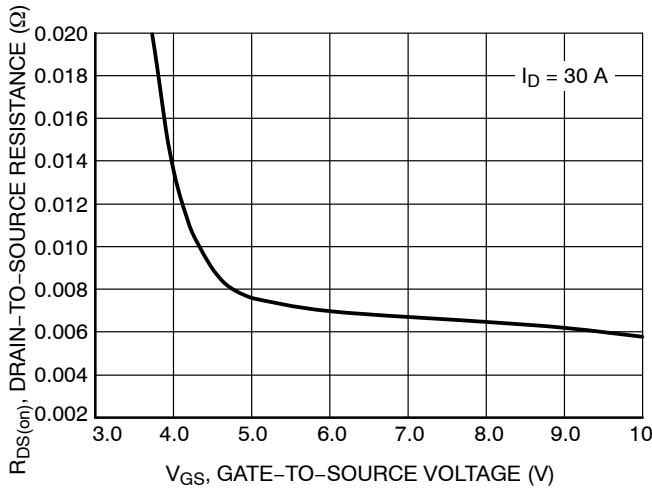


Figure 3. On-Resistance vs. V_{GS}

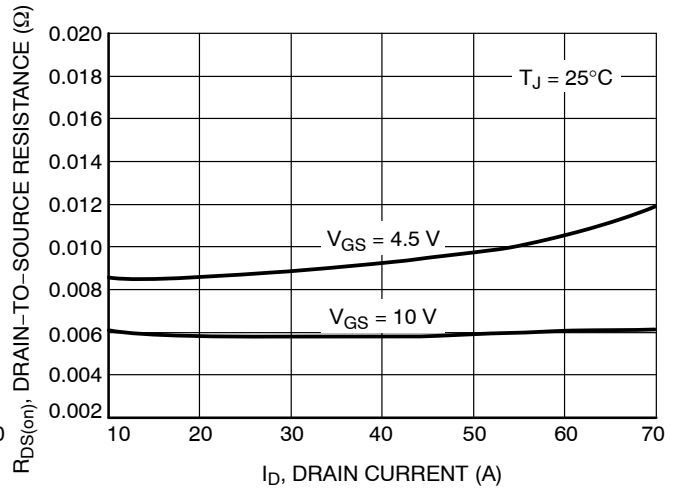


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

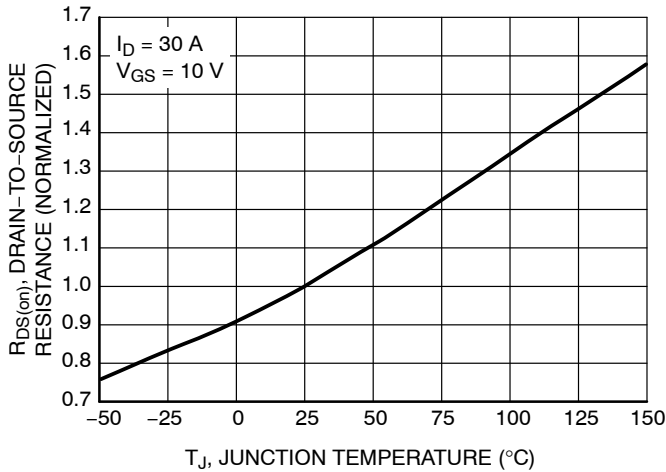


Figure 5. On-Resistance Variation with Temperature

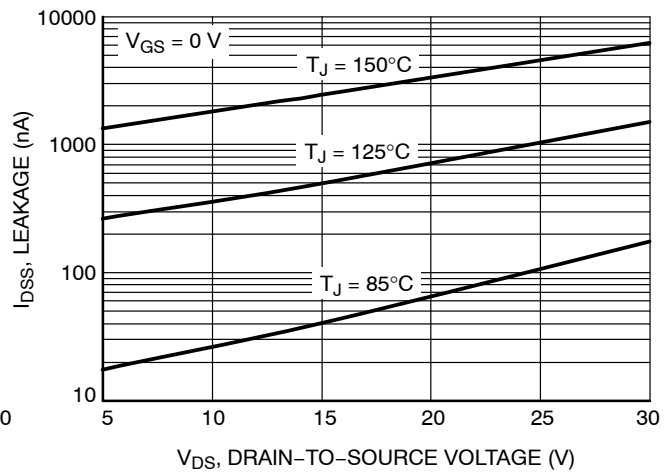


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS – Q1

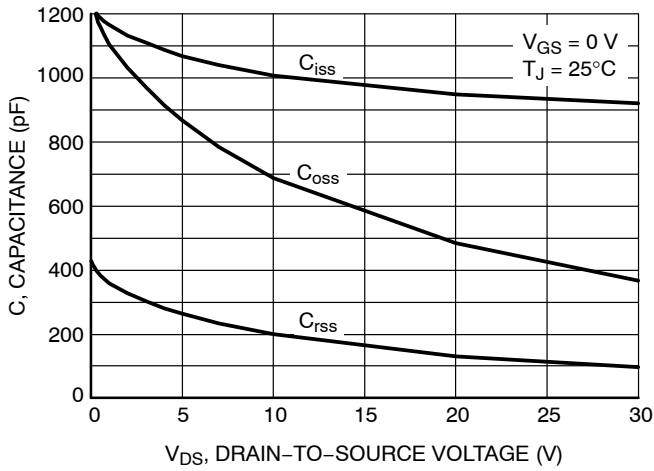


Figure 7. Capacitance Variation

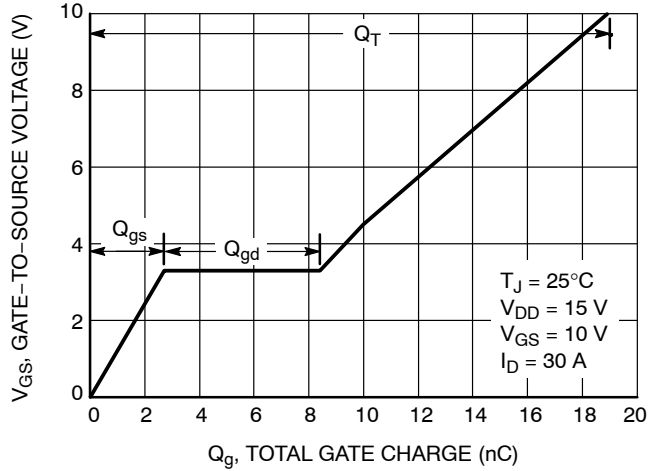


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

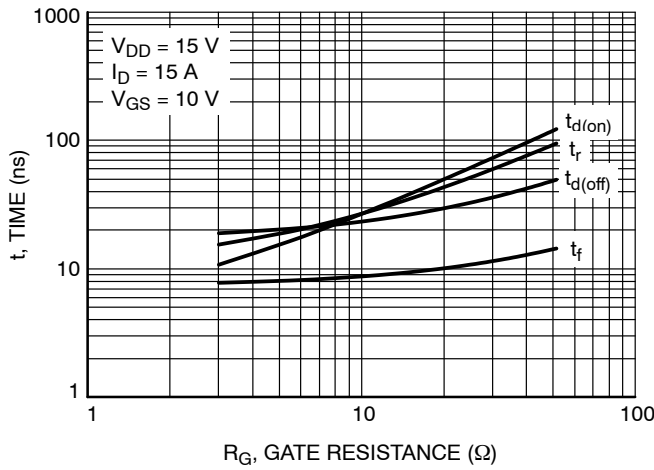


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

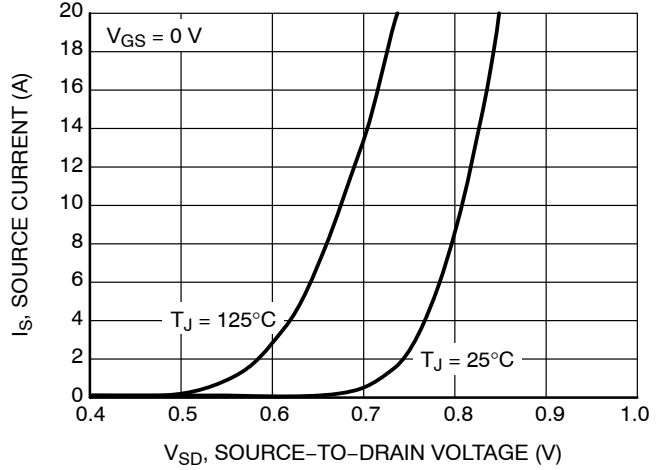


Figure 10. Diode Forward Voltage vs. Current

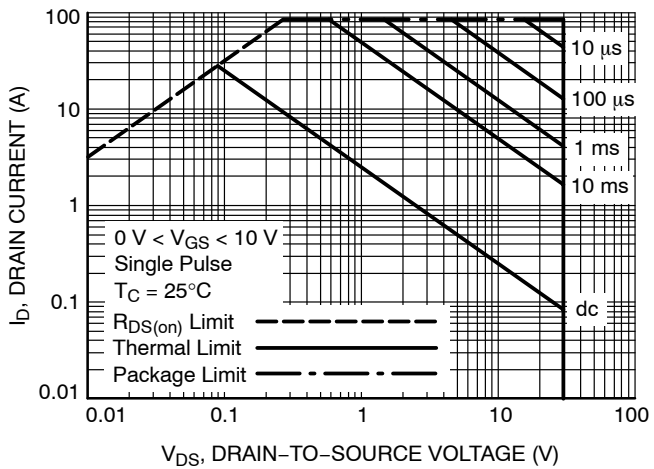


Figure 11. Maximum Rated Forward Biased Safe Operating Area

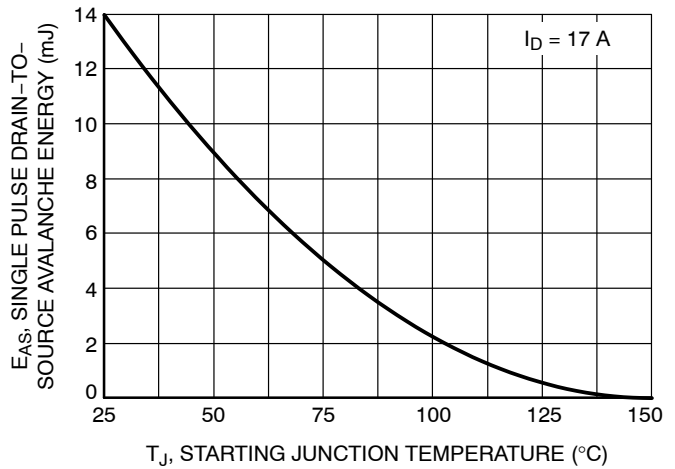


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS – Q1

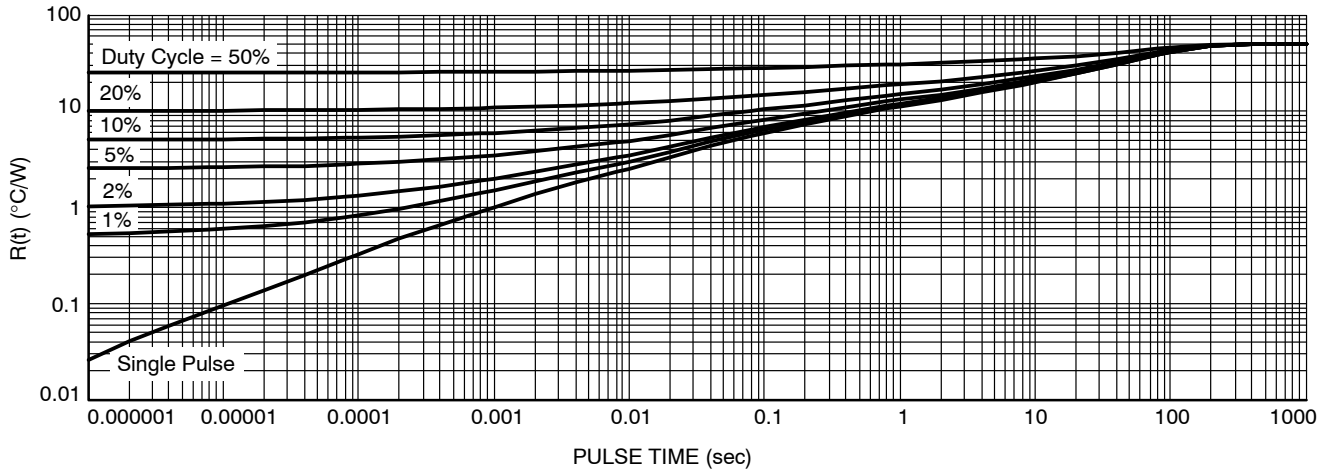


Figure 13. Thermal Response

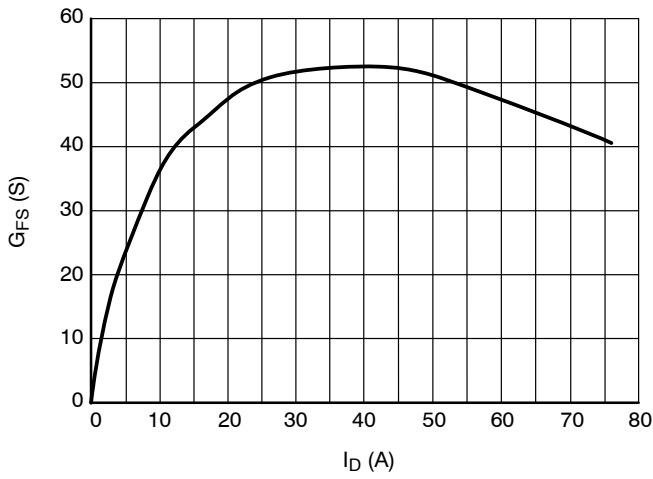


Figure 14. G_{FS} vs. I_D

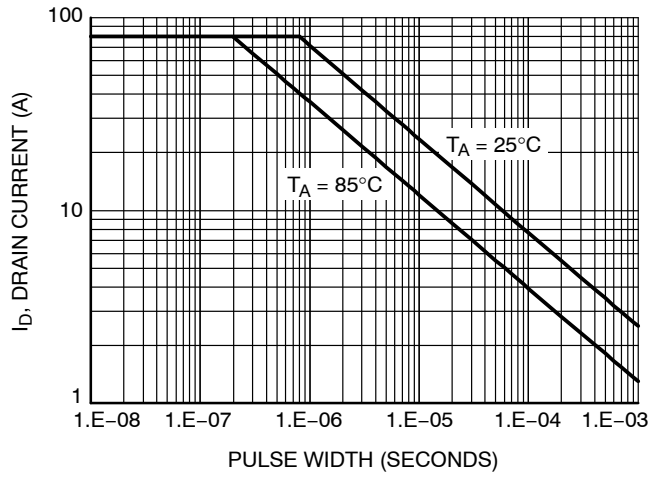


Figure 15. Avalanche Characteristics

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TYPICAL CHARACTERISTICS – Q2

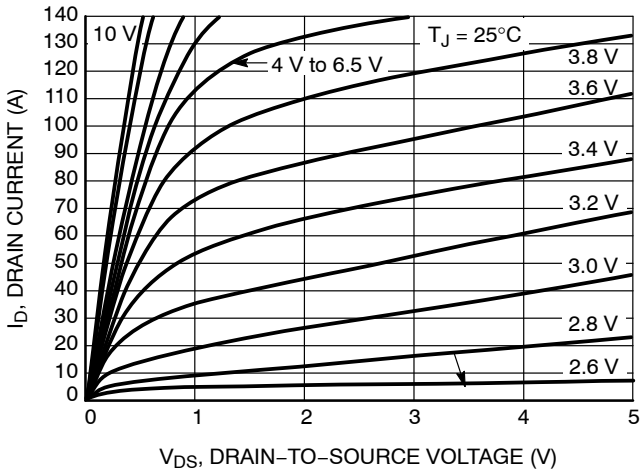


Figure 16. On-Region Characteristics

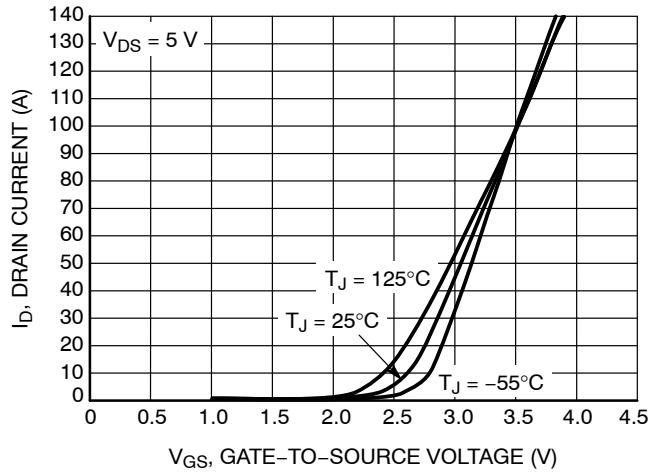


Figure 17. Transfer Characteristics

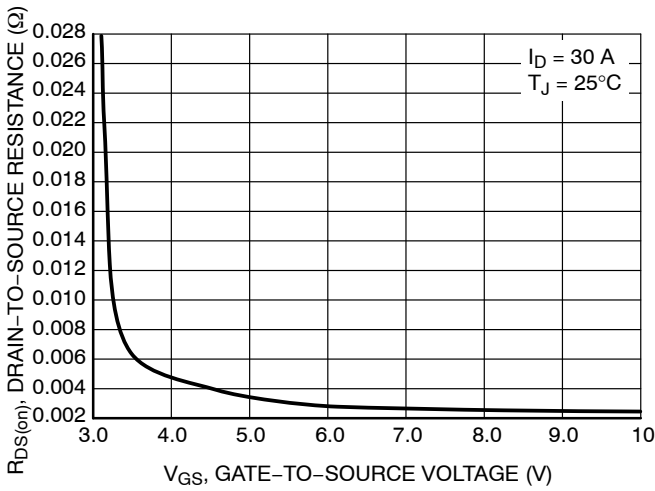


Figure 18. On-Resistance vs. V_{GS}

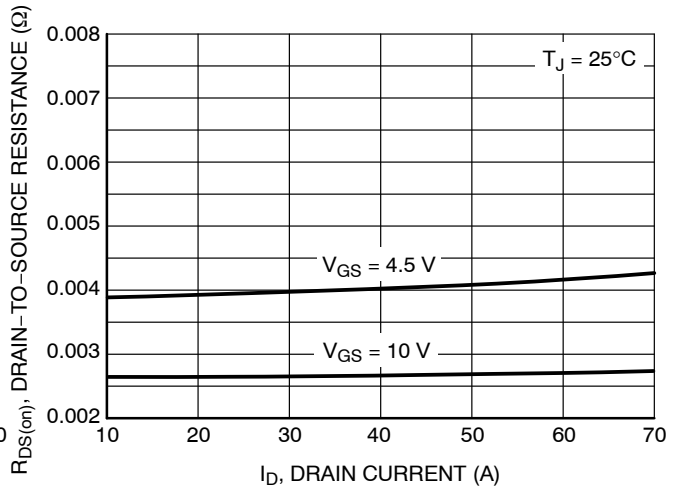


Figure 19. On-Resistance vs. Drain Current and Gate Voltage

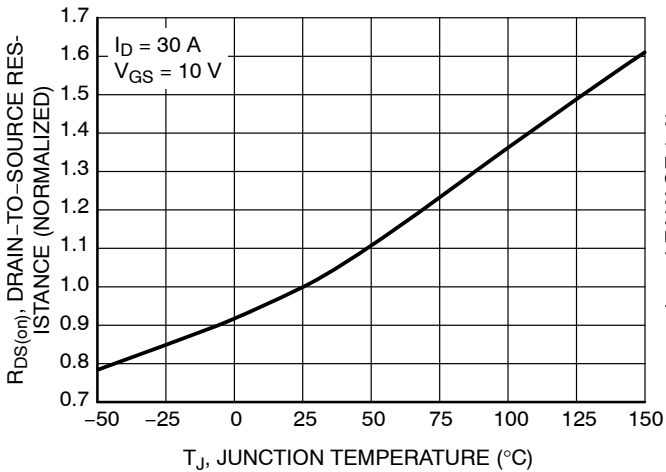


Figure 20. On-Resistance Variation with Temperature

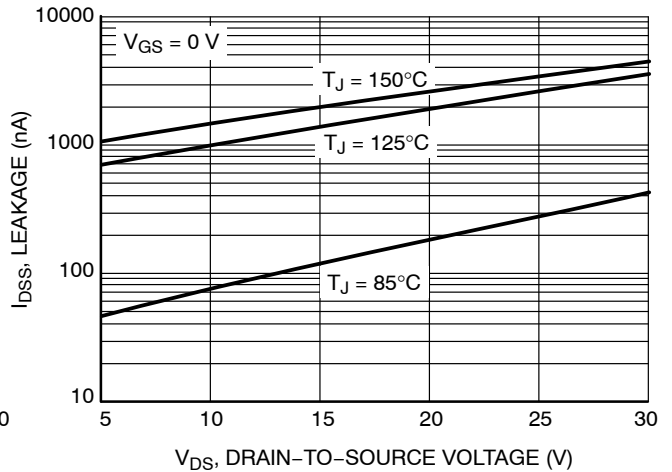


Figure 21. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS – Q2

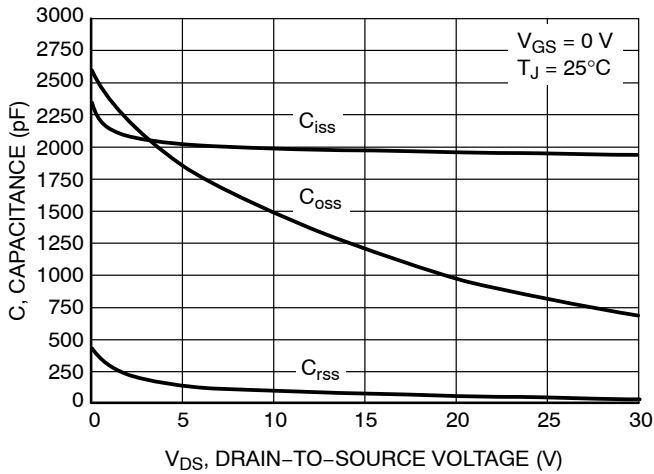


Figure 22. Capacitance Variation

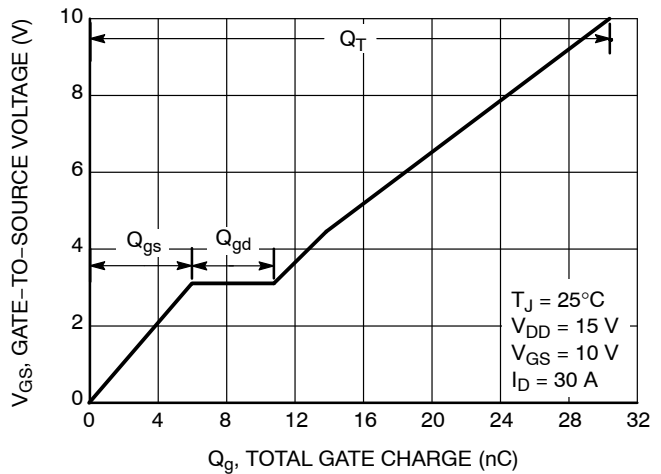


Figure 23. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

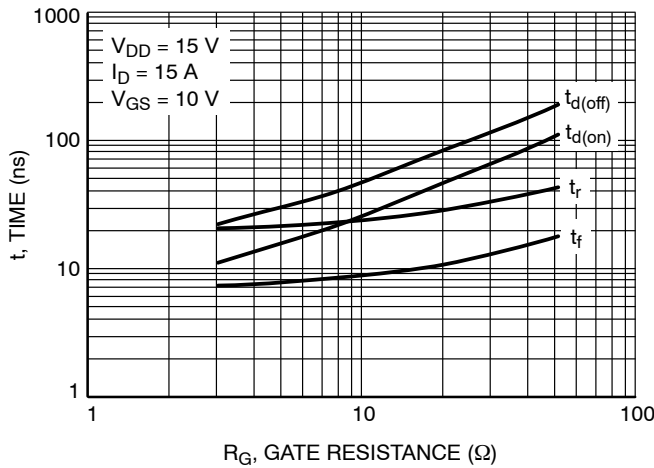


Figure 24. Resistive Switching Time Variation vs. Gate Resistance

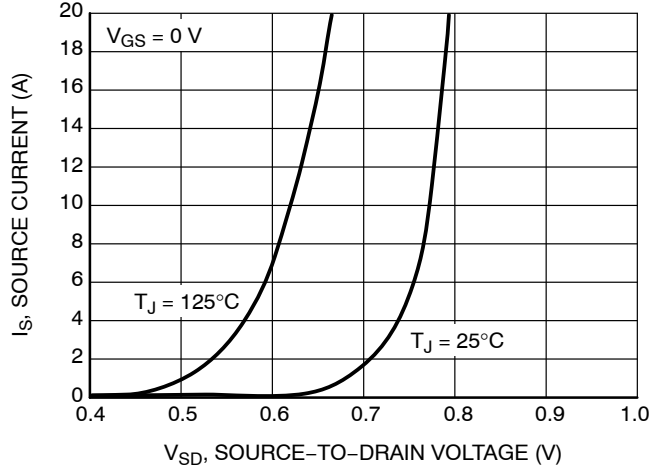


Figure 25. Diode Forward Voltage vs. Current

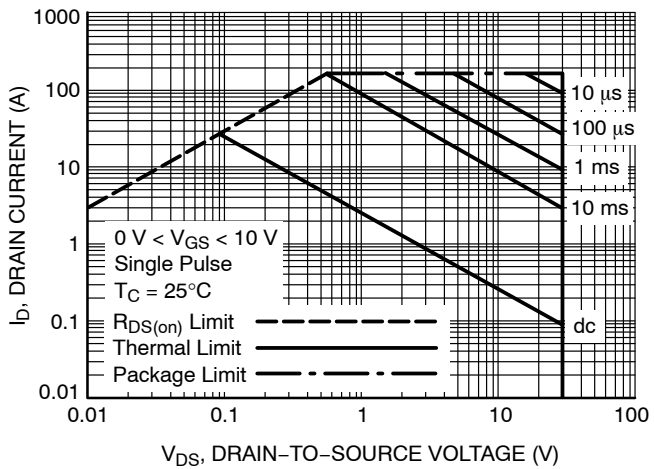


Figure 26. Maximum Rated Forward Biased Safe Operating Area

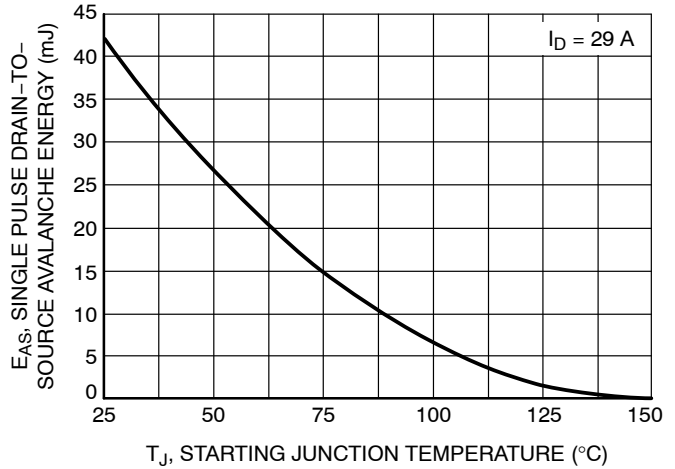


Figure 27. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS – Q2

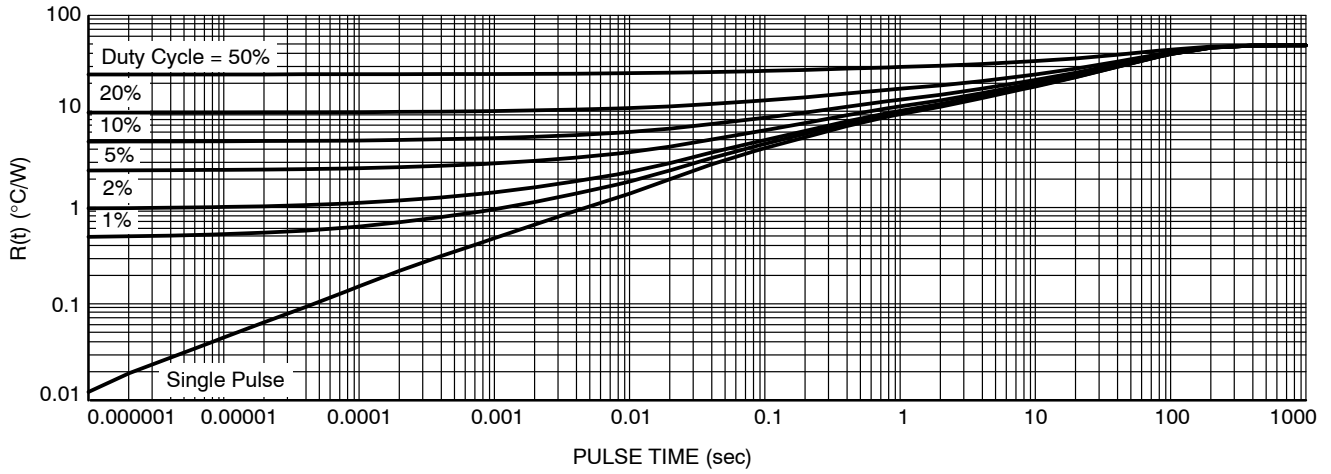


Figure 28. Thermal Response

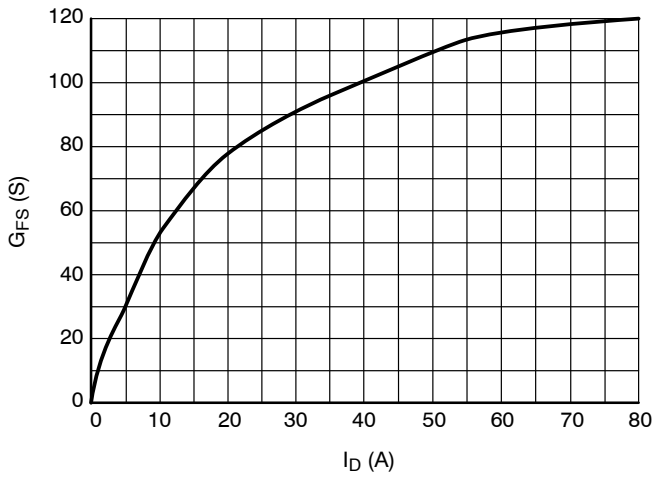


Figure 29. G_{FS} vs. I_D

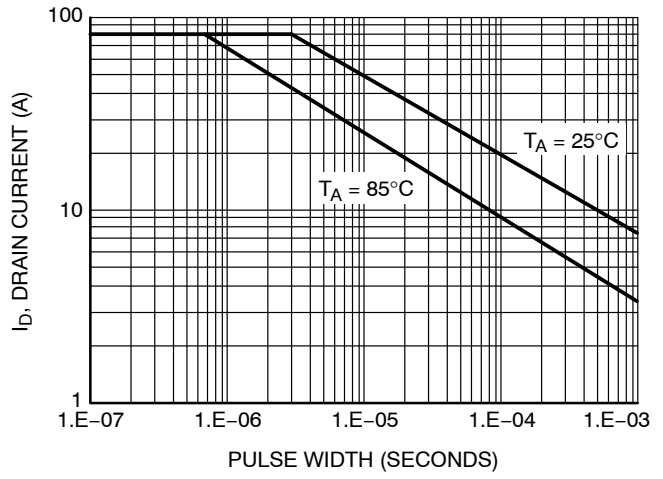


Figure 30. Avalanche Characteristics

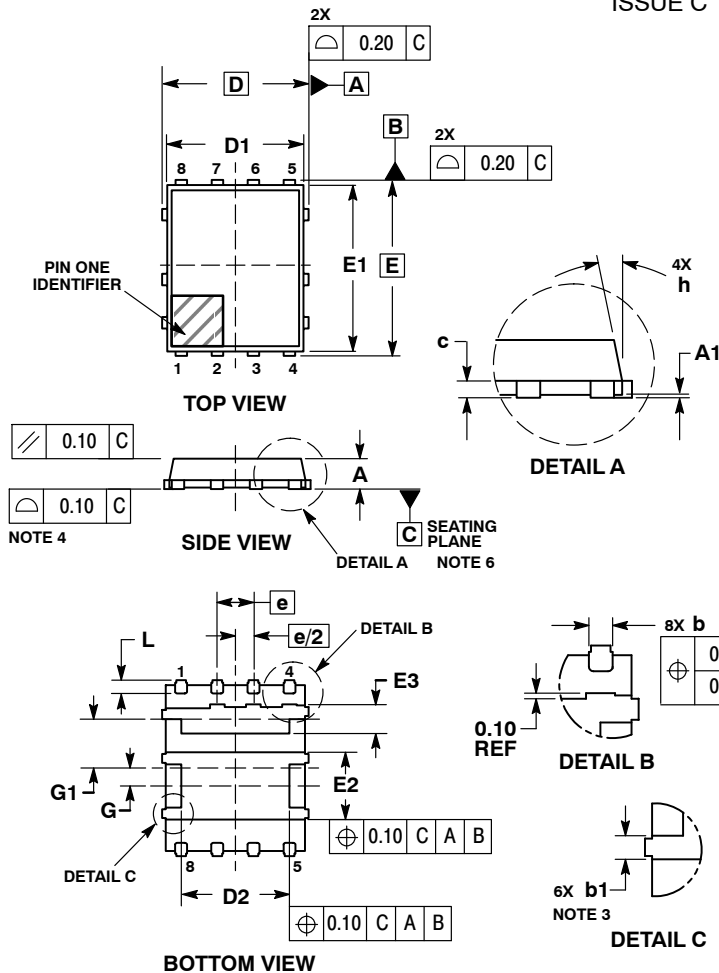
NTMFD4C20N

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL-Dual-Asymmetrical)

CASE 506BX

ISSUE C

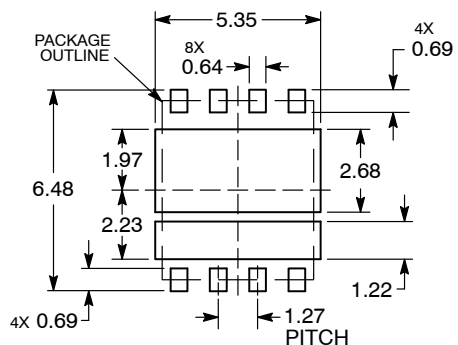


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b AND b1 APPLY TO PLATED FEATURES AND ARE MEASURED BETWEEN 0.15 AND 0.25 MM FROM TERMINAL TIPS.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
A1	0.00	0.05
b	0.41	0.61
b1	0.41	0.61
c	0.23	0.33
D	5.15 BSC	
D1	4.50	5.10
D2	3.50	4.22
E	6.15 BSC	
E1	5.50	6.10
E2	2.27	2.67
E3	0.82	1.22
e	1.27 BSC	
G	0.63 BSC	
G1	1.72 BSC	
h	---	12 °
L	0.35	0.55

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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